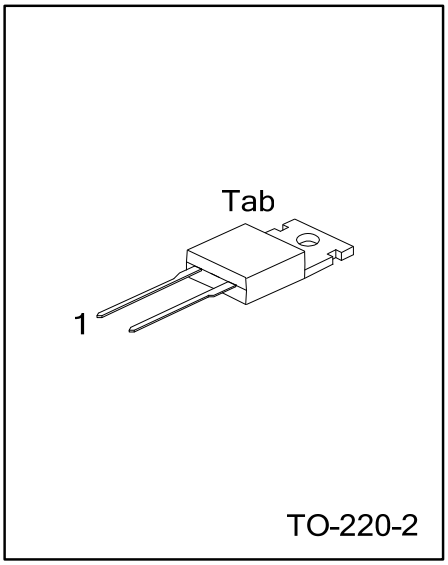
ULTRAFAST, LOW SWITCHING LOSS RECTIFIER DIODE



■ DESCRIPTION

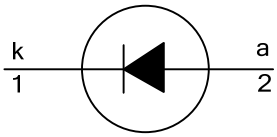
The UTC **BYC8-600** is a rectifier diode. It provides the designers with ultra-fast switching and low switching loss in associated MOSFET.

The UTC **BYC8-600** is generally applied in continuous current mode(CCM), power factor correction (PFC), half-bridge lighting ballasts and half-bridge/full-bridge switched mode power supplies.

■ FEATURES

* Low Reverse Recovery Current
* Ultra-Fast Switching
* Low Switching Loss In Associated MOSFET
* Low Thermal Resistance

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free Plating	Halogen Free		1	2	Tab	
BYC8L-600-TA2-T	BYC8G-600-TA2-T	TO-220-2	K	A	K	Tube

Note: Pin Assignment: A: Anode, K: Cathode, Tab: Mounting Base

BYC8L-600-TA2-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube (2) TA2: TO-220-2 (3) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Peak Repetitive Reverse Voltage		V_{RRM}	600	V
Crest Working Reverse Voltage		V_{RWM}	600	V
Average Forward Current	square-wave pulse;δ =0.5; T_{Tab} ≤109°C	$I_{F(AV)}$	8	A
Repetitive Peak Forward Current	square-wave pulse; δ =0.5; t_P = 25μs, T_{Tab} ≤109°C	I_{FRM}	16	A
Non-Repetitive Peak Forward Current.	t_P=8.3ms,sine-wave pulse;T_J =150°C	I_{FSM}	60	A
	t_P=10ms,sine-wave pulse;T_J =150°C		55	A
Operating Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$θ_{JA}$	60	K/W
Junction to Tab	$θ_{JB}$	2.2	K/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Forward Voltage	V_F	I_F =8A, T_J =25°C			2	2.9	V
		I_F =8A, T_J =150°C			1.4	1.85	V
		I_F =16A, T_J =150°C			1.7	2.3	V
Reverse Current	I_R	V_R=600V			9	150	μA
		V_R=500V, T_J=100°C			1.1	3	mA
Recovered Charge	Q_R	I_F =1A, dI_F/dt=100A/μs, T_J =25°C			12		nC
Reverse Recovery Time	t_{RR}	I_F =1A, V_R=30V, dI_F/dt=50A/μs, T_J =25°C			30	52	ns
		I_F=8A,V_R=400V, dI_F/dt=500A/μs	T_J=100°C		32	40	ns
			T_J=25°C (See Figure1)		19		ns
Peak Reverse Recovery Current	I_{RM}	I_F=8A,V_R=400V, dI_F/dt=50A/μs, T_J=125°C			1.5	5.5	A
		I_F=8A,V_R=400V, dI_F/dt=500A/μs, T_J=100°C			9.5	12	A
Forward Recovery Voltage	V_{FR}	I_F =10A, dI_F/dt=100A/μs(See Figure2)			8	10	V

■ TYPICAL CHARACTERISTICS

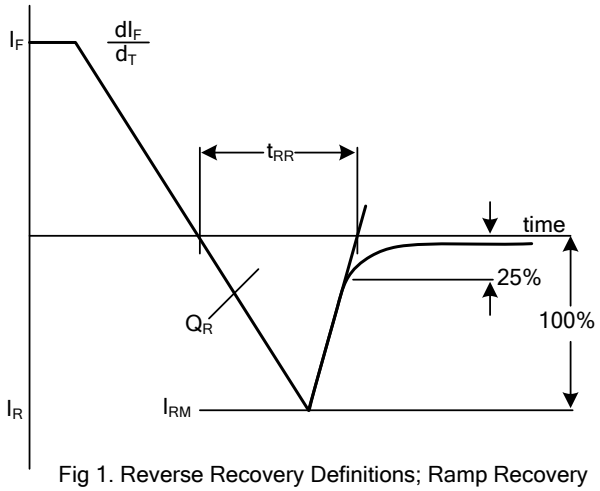


Fig 1. Reverse Recovery Definitions; Ramp Recovery

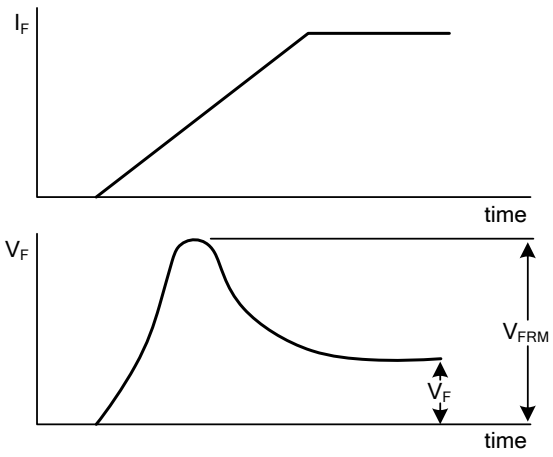


Fig 2. Forward Recovery Definitions